Title: High-Electron Mobility Transistor With Zinc Oxide Inventors: Jeff Nause, Shanthi Ganesan Atty Dkt. No.:046361/265061

FIGURE 1

1/2

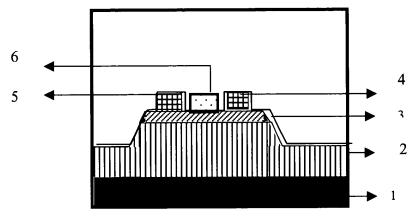


Figure 1: Layer Structure of the HEMT

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FIGURE 2

2/2

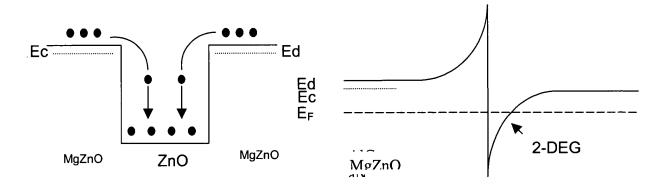


Figure 2: Band diagram showing the band bending and formation of 2DEG electron gas